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- (71) **Applicant:** **INTERNATIONAL BUSINESS MACHINES CORPORATION** [US/US]; New Orchard Road, Armonk, New York 10504 (US).
- (71) **Applicant (for MG only):** **IBM (CHINA) CO., LIMITED** [CN/CN]; 7F, Bldg 10, Zhang Jiang Innovation Park, 399 Keyuan Road, Zhang Jiang High-Tech Campus, Pudong New Area, Shanghai 201203 (CN).
- (72) **Inventors:** **GONG, Nanbo**; 1101 Kitchawan Road, Yorktown Heights, New York 10598 (US). **ANDO, Takashi**; 1101 Kitchawan Road, Yorktown Heights, New York 10598 (US). **COHEN, Guy, M.**; 1101 Kitchawan Road, Yorktown Heights, New York 10598 (US).
- (74) **Agent:** **CCPIT PATENT AND TRADEMARK LAW OFFICE**; 10/F, Ocean Plaza, 158 Fuxingmennei Street, Beijing 100031 (CN).
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(54) **Title:** SEMICONDUCTOR LOGIC CIRCUITS INCLUDING NON-VOLATILE MEMORY CELL

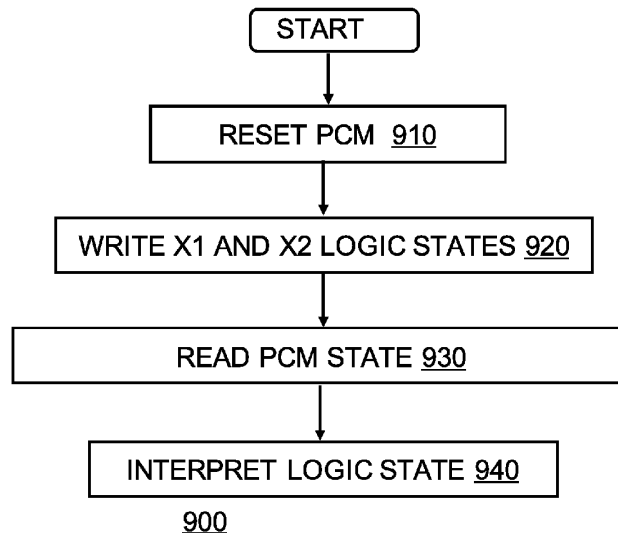


Fig. 9

(57) **Abstract:** A phase change memory (PCM) device including a bottom electrode, a bottom heater over the bottom electrode, a bottom buffer layer over the bottom heater, a PCM region over the bottom buffer layer, a top buffer layer over the PCM region, a top heater over the top buffer layer, and a top electrode over the top heater.

[Continued on next page]

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